

Midium Power Transistors (-50V / -3A)

2SAR533D

● Features

- 1) Low saturation voltage, typically
 $V_{CE(sat)} = -0.4V$ (Max.) ($I_C / I_B = -1A / -50mA$)
- 2) High speed switching

● Structure

PNP Silicon epitaxial planar transistor

● Applications

Driver

● Packaging specifications

Type	Package	CPT3
	Code	TL
	Basic ordering unit (pieces)	2500

● Absolute maximum ratings (Ta = 25°C)

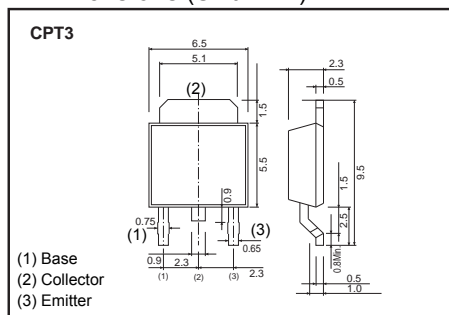
Parameter	Symbol	Limits	Unit	
Collector-base voltage	V_{CBO}	-50	V	
Collector-emitter voltage	V_{CEO}	-50	V	
Emitter-base voltage	V_{EBO}	-6	V	
Collector current	DC	I_C	-3	A
	Pulsed	I_{CP}^{*1}	-6	A
Power dissipation	P_D^{*2}	1	W	
	P_D^{*3}	10	W	
Junction temperature	T_j	150	°C	
Range of storage temperature	T_{stg}	-55 to 150	°C	

*1 Pw=10ms, Single Pulse

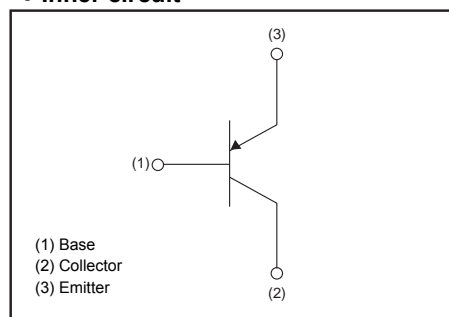
*2 Mounted on a substrate.

*3 Tc=25°C

● Dimensions (Unit : mm)



● Inner circuit



● Electrical characteristic (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BV_{CEO}	-50	-	-	V	$I_C = -1\text{mA}$
Collector-base breakdown voltage	BV_{CBO}	-50	-	-	V	$I_C = -100\mu\text{A}$
Emitter-base breakdown voltage	BV_{EBO}	-6	-	-	V	$I_E = -100\mu\text{A}$
Collector cut-off current	I_{CBO}	-	-	-1	μA	$V_{CB} = -50\text{V}$
Emitter cut-off current	I_{EBO}	-	-	-1	μA	$V_{EB} = -4\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}^{*1}$	-	-200	-400	mV	$I_C = -1\text{A}$, $I_B = -50\text{mA}$
DC current gain	h_{FE}	180	-	450	-	$V_{CE} = -3\text{V}$, $I_C = -50\text{mA}$
Transition frequency	f_T^{*1}	-	300	-	MHz	$V_{CE} = -10\text{V}$ $I_E = 500\text{mA}$, $f = 100\text{MHz}$
Collector output capacitance	C_{ob}	-	24	-	pF	$V_{CB} = -10\text{V}$, $I_E = 0\text{A}$ $f = 1\text{MHz}$
Turn-on time	t_{on}^{*2}	-	45	-	ns	$I_C = -1.5\text{A}$, $I_{B1} = -150\text{mA}$, $I_{B2} = 150\text{mA}$, $V_{CC} = -10\text{V}$
Storage time	t_{stg}^{*2}	-	250	-	ns	
Fall time	t_f^{*2}	-	35	-	ns	

*1 Pulsed

*2 See switching time test circuit

●Electrical characteristic curves (Ta = 25°C)

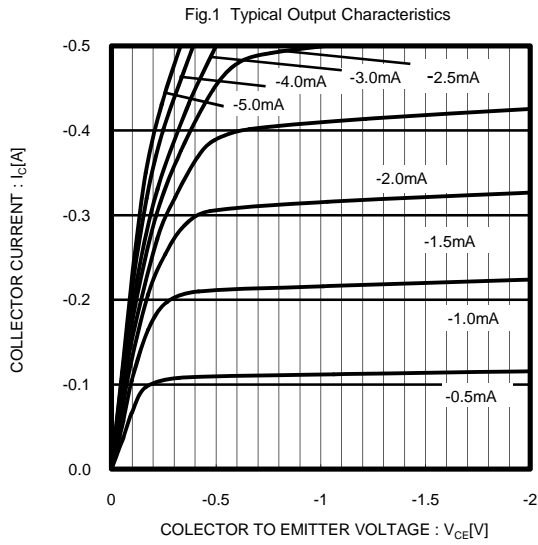


Fig.3 DC Current Gain vs. Collector Current (II)

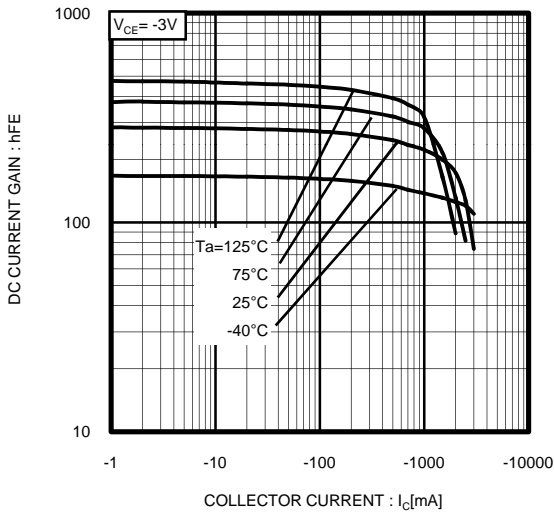


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current

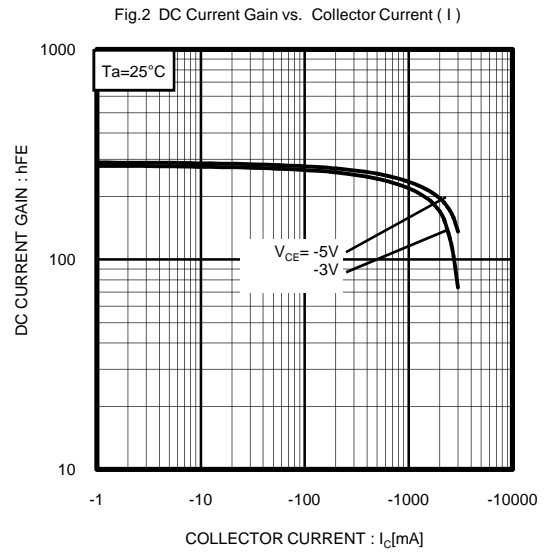
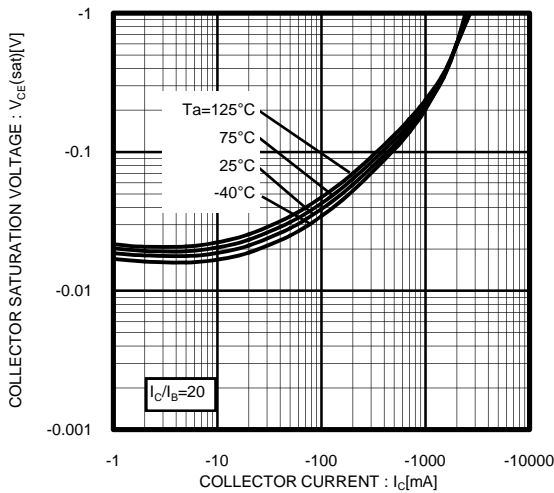


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current (I)

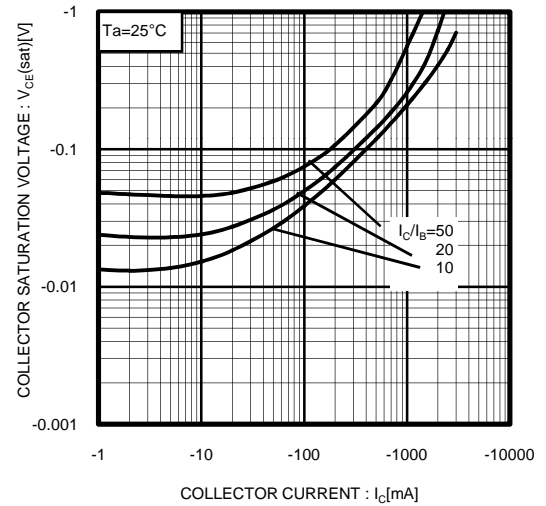
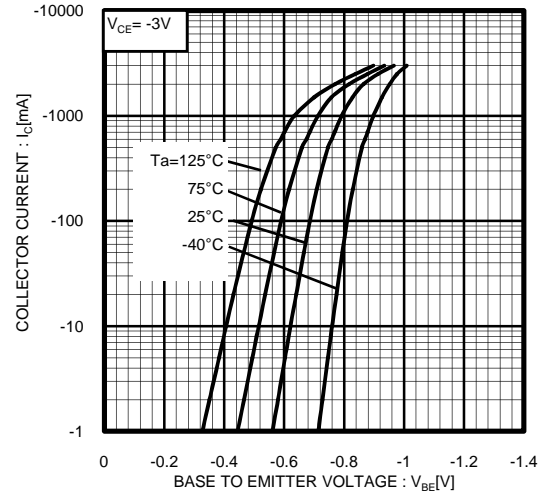
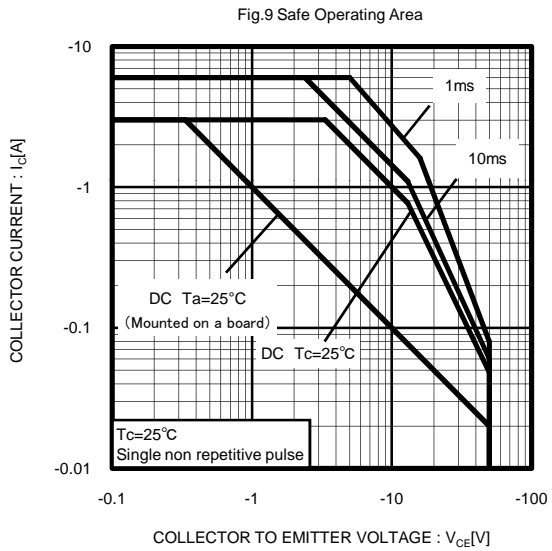
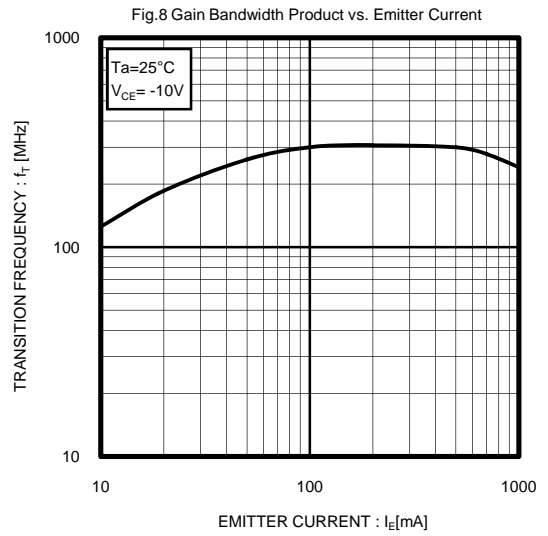
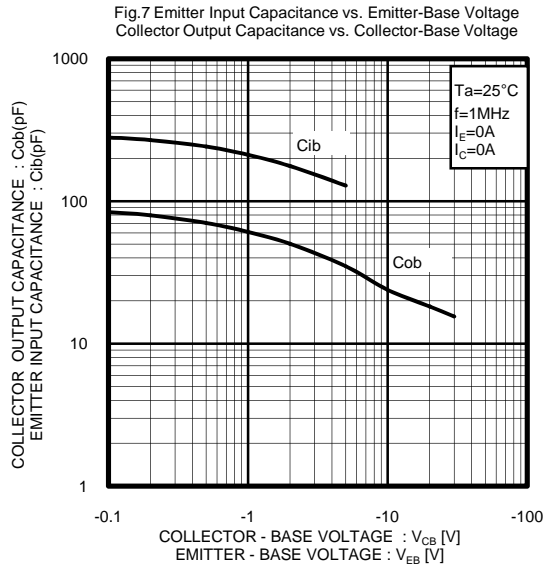
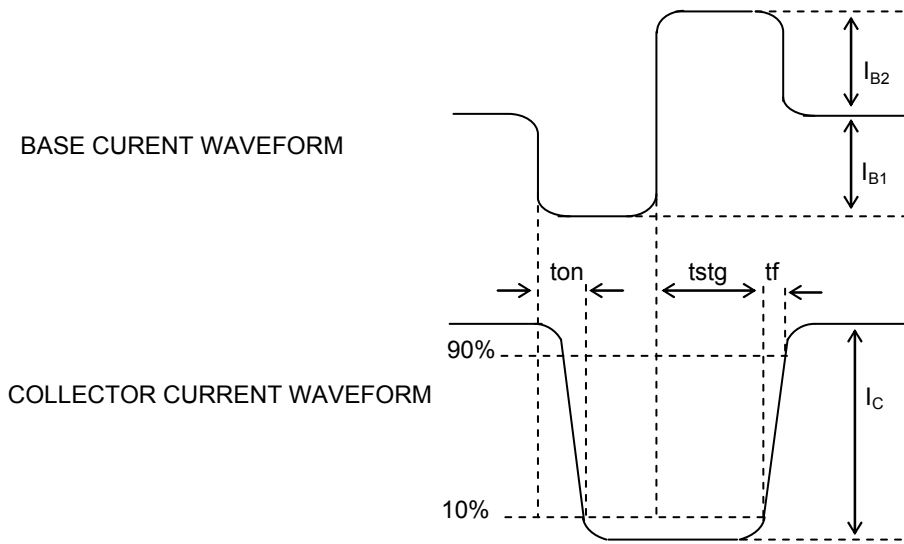
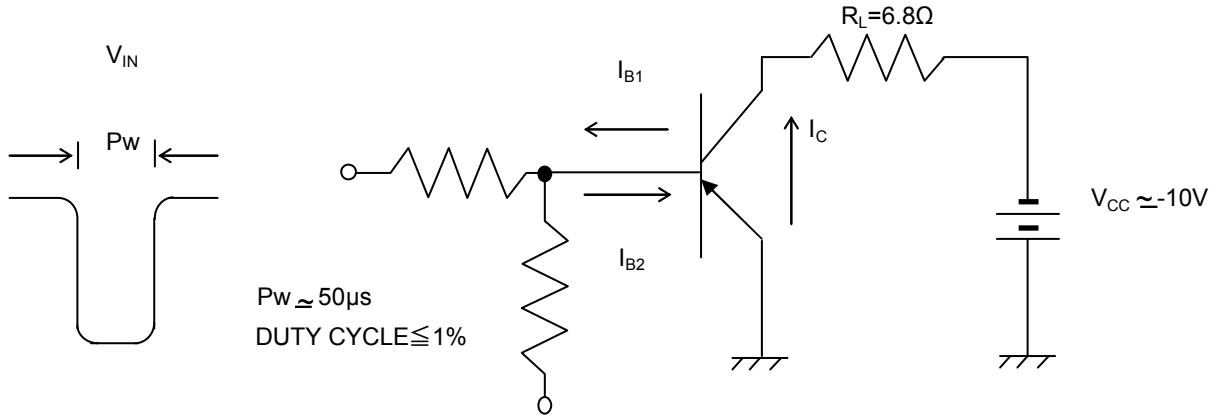


Fig.6 Ground Emitter Propagation Characteristics





● Switching time test circuit



Notes

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